

# **Engineering/Process Change Notice**

**ECN/PCN No.: 4457** 

For Manufacturer					
Product Description: Ceramic SMD Crystal Oscillator	Abracon Part Numb EH25 Series	er / Part Series:	<ul><li>□ Documentation only</li><li>⋈ ECN</li><li>⋈ EOL</li></ul>	Series     □ Part Number	
Affected Revision:	New Revision:		Application:	☐ Safety	
Rev. G 06/08/2012	E	DL		Non-Safety	
Prior to Change: ACTIVE					
After Change: EOL					
Cause/Reason for Change: Discontinuation of manufacturing capability					
	Chan	ge Plan			
<b>Effective Date:</b> 11/15/2022	Additional Remarks: N/A				
Change Declaration: N/A					
Issued Date: 11/15/22	Issued By:  Conor Healey		Issued Department: Engineering		
Approval:	Approval:		Approval:		
Thomas Culhane	Reuben Q		Ying Huang		
Engineering Director	Quality		Purchasing Dir	ector	
	For Abrac	on EOL only			
Last Time Buy (if applicable):	Alternate Part Numb				
02-15-2023 ASL, FO7HH					
Based upon material availability, contact					
Additional Approval:	Additional Approval	:	Additional Approval:		
Customer Approval (If Applicable)					
Qualification Status:					
$\Box$ Approved $\Box$ Not accepted Note: It is considered approved if there is no feedback from the customer 1 month after ECN/PCN is released.					
Customer Part Number:		<b>Customer Project:</b>			
Company Name:	Company Represent	ative:	Representative Signature	:	
Customer Remarks:					



Form #7020 | Rev. G | Effective: 02/22/2021 |













#### **REGULATORY COMPLIANCE**











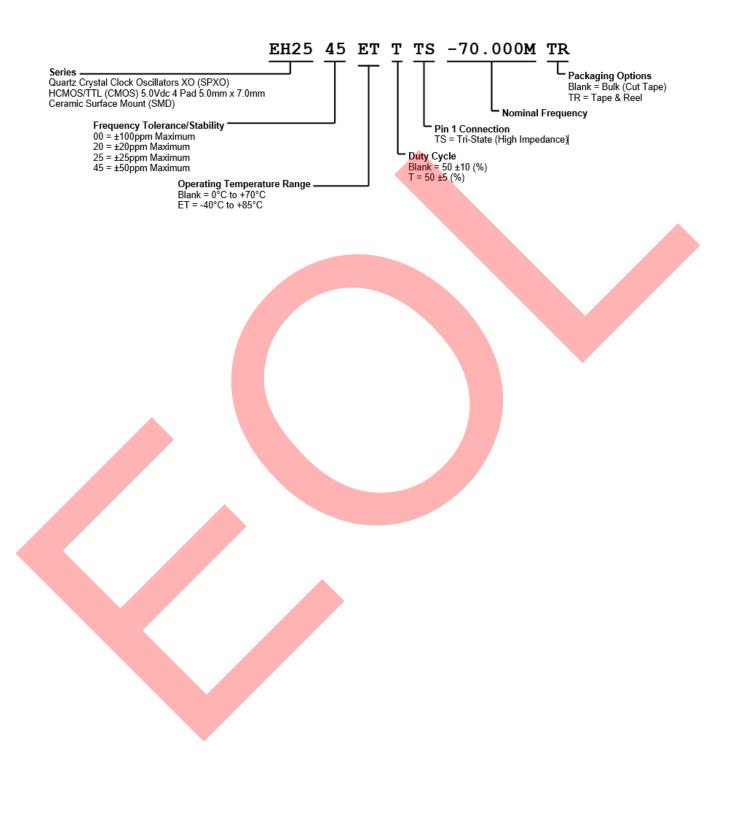
#### **ITEM DESCRIPTION**

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 4 Pad 5.0mm x 7.0mm Ceramic Surface Mount (SMD)

ELECTRICAL SPECIFICATIONS				
Nominal Frequency	1MHz to 155.52MHz			
Frequency Tolerance/Stability	Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration ±100ppm Maximum ±20ppm Maximum ±25ppm Maximum ±50ppm Maximum			
Aging at 25°C	±5ppm/year Maximum			
Operating Temperature Range	0°C to +70°C -40°C to +85°C			
Supply Voltage	5.0Vdc ±10%			
Input Current	No Load 50mA Maximu <mark>m</mark>			
Output Voltage Logic High (Voh)	IOH= -16mA 2.4Vdc Minim <mark>um wit</mark> h TTL Load, Vdd-0.4Vdc Minimum with H <mark>CMOS L</mark> oad			
Output Voltage Logic Low (Voi)	IOL= +16mA 0.4Vdc Maxim <mark>um wit</mark> h TTL Load, 0.5Vdc Maximum with HCMO <mark>S Load</mark>			
Rise/Fall Time	Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load 6nSec Maximum over Nominal Frequency of 1MHz to 70MHz 4nSec Maximum over Nominal Frequency of 70.000001MHz to 155.52MHz			
Duty Cycle	50 ±10 (%) (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load over Nominal Frequency range of 1MHz to 70MHz; Measured at 50% of waveform with TTL Load or with HCMOS Load over Nominal Frequency range of 70.000001MHz to 155.52MHz) 50 ±5 (%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)			
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum over Nominal Frequency of 1MHz to 70MHz 5TTL Load or 15pF HCMOS Load Maximum over Nominal Frequency of 70.000001MHz to 155.52MHz			
Output Logic Type	CMOS			
Pin 1 Connection	Tri-State (High Impedance)			
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.			
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical			
One Sigma Clock Period Jitter	±50pSec Maximum, ±30p <mark>Sec Typic</mark> al			
Start Up Time	10mSec Maximum			
Storage Temperature Range	-55°C to +125°C			

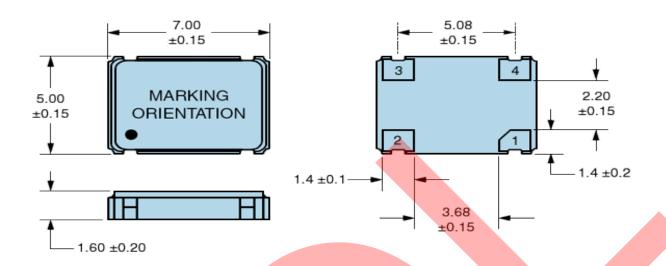


#### **PART NUMBERING GUIDE**

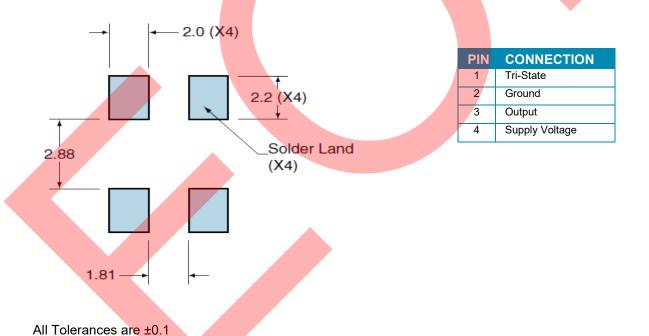




#### **MECHANICAL DIMENSIONS**



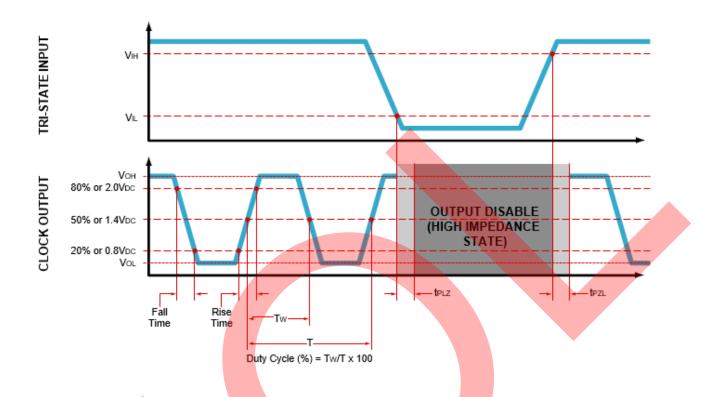
#### SUGGESTED SOLDER PAD LAYOUT



**All Dimensions in Millimeters** 

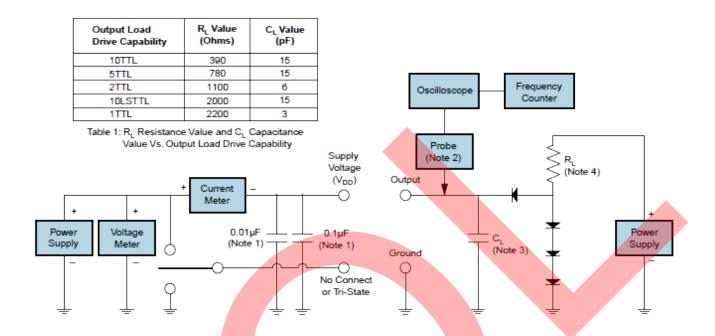


#### **OUTPUT WAVEFORM & TIMING DIAGRAM**





#### **TEST CIRCUIT FOR TTL OUTPUT**



Note 1: An external 0.1μF low frequency tantalum bypass capacitor in parallel with a 0.01μF high frequency ceramic bypass Capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attentuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive Probe is recommended.

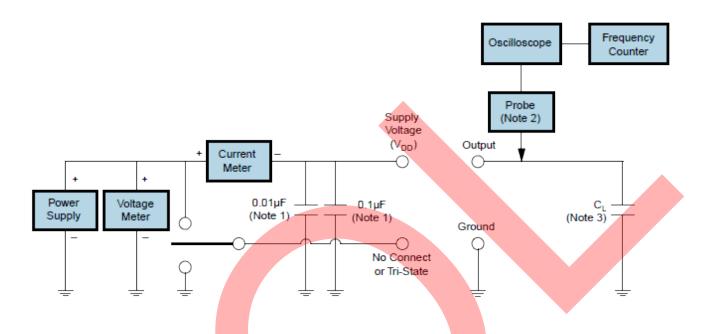
Note 3: Capacitance value C<sub>L</sub> includes sum of all probe and fixture capacitance.

Note 4: Resistance value R<sub>L</sub> is shown in Table 1. See applicable specification sheet for †Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



### **TEST CIRCUIT FOR CMOS OUTPUT**



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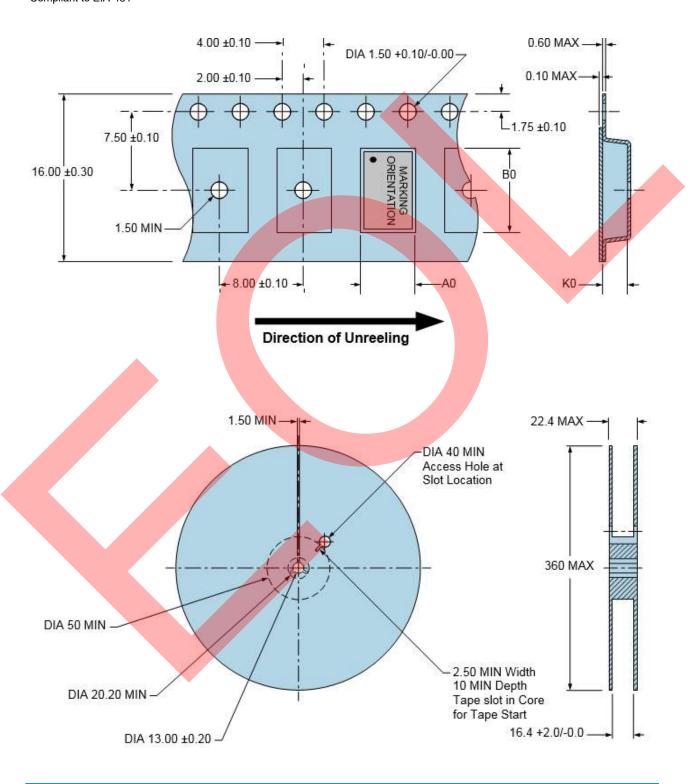
Note 3: Capacitance value C<sub>L</sub> includes sum of all probe and fixture capacitance.



#### **TAPE & REEL DIMENSIONS**

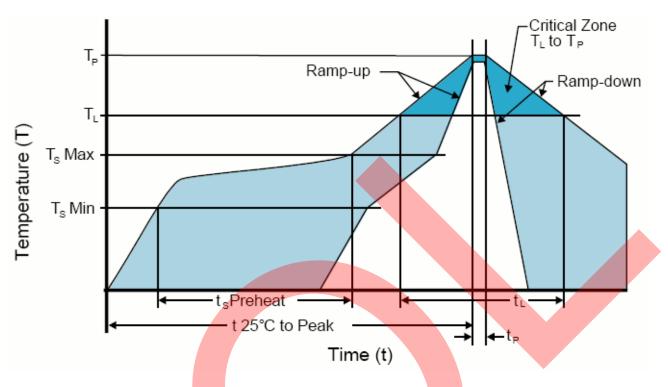
Quantity per Reel: 1,000 Units

All Dimensions in Millimeters
Compliant to EIA-481





## **RECOMMENDED SOLDER REFLOW METHOD**



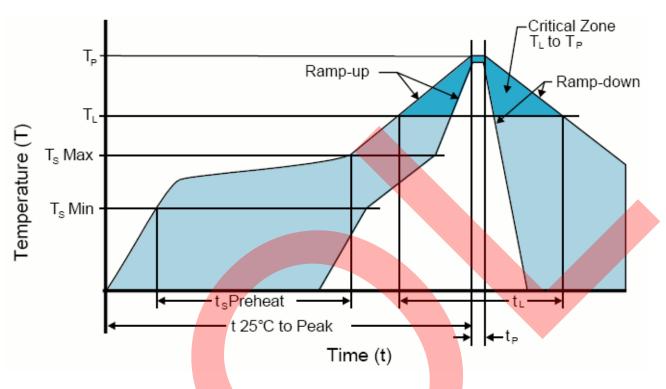
HIGH TEMPERATURE INFRARED/CONVECTION		
T <sub>S</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	3°C/Second Maximum	
Preheat		
- Temperature Minimum (T <sub>S</sub> MIN)	150°C	
- Temperature Typical (T <sub>s</sub> TYP)	175°C	
- Temperature Maximum(T <sub>s</sub> MAX)	200°C	
- Time (ts MIN)	60 - 180 Seconds	
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/Second Maximum	
Time Maintained Above:		
- Temperature (T <sub>L</sub> )	217°C	
- Time (t <sub>L</sub> )	60 - 150 Secon <mark>ds</mark>	
Peak Temperature (T <sub>P</sub> )	260°C Maxim <mark>um for 1</mark> 0 Seconds Maximum	
Target Peak Temperature(T <sub>P</sub> Target)	250°C + <mark>0/-5°C</mark>	
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 Seconds	
Ramp-down Rate	6°C/Second Maximum	
Time 25°C to Peak Temperature (t)	8 Minutes Maximum	
Moisture Sensitivity Level	Level 1	
Additional Notes	Temperatures shown are applied to body of device.	

#### **High Temperature Manual Soldering**

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)



#### RECOMMENDED SOLDER REFLOW METHOD



LOW TEMPERATURE INFRARED/CONVECTION 240°C			
T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/Second Maximum		
Preheat			
- Temperature Minimum (T <sub>s</sub> MIN)	N/A		
- Temperature Typical (T <sub>s</sub> TYP)	150°C		
- reinperature waxiiiium(r. wax)	N/A		
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds		
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	5°C/Second Maximum		
Time Maintained Above:			
- Temperature (T <sub>L</sub> )	150°C		
- Time (t <sub>L</sub> )	200Seconds Ma <mark>ximum</mark>		
Peak Temperature (T <sub>P</sub> )	240°C		
Target Peak Temperature(TP Target)	240°C M <mark>aximum 2</mark> Times/230°C Maximum 1Time		
Time within 5°C of actual peak (tp)	10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time		
Ramp-down Rate	5°C/Second Maximum		
Time 25°C to Peak Temperature (t)	N/A		
Moisture Sensitivity Level	Level 1		
Additional Notes	Temperatures shown are applied to body of device.		

#### **Low Temperature Manual Soldering**

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)